Sheet 1	of	1							
INFOR	ITAN	ON	DISOLÓSURE	ATTY.	DOCKET NO.	SERIA	L NO.		
CITATION		340-	80	10/6	86,520				
		1	nn a Denne I	APPLIC	CANT				
		ŀ	. N. 1 9 2005 €	KOC	CHERGIN et al.			·	
(Ua	CEVO (2	shee	PAO FAMILIA	FILING	DATE	TC/A.U).		
			RADRUM	160	ctober 2003	2883			
				ŧ	U.S. PATENT DOCUMENTS				
'EXAMINER			JMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING DATE IF APPROPRIAT
	+				/1				· _
					 			 	

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPROPRIATE
			/			•
	-					
			 			
			 			
			 			
			 	- 		
						
			 			
			 			
			<u> </u>			
		ļ			 	
					<u> </u>	
		<u> </u>				
			L _ /		ļ	
			l/		<u> </u>	<u> </u>
		FQ	REIGN PATENT DOCUMENTS			
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
			/ .			
			/			
			1 7			
						
		 	- <i> </i>		 	
		 	 /			
			 /. 		 	
	OTHER DOC	IMENTS (including Author, Title, Date, Pertine	nt pages, e	tc.)	
	Vladimir Kochergin "C)moidirectio	nal Optical Filters," Kluwer Academic Pub	lishers (200	3)	
742	Vaccinati Recentingui, C	A THINITE OF THE PARTY OF THE P	/			
			_/			
			1			—
			1			
·····		V				
	Chus Kale					
			_	7	20	
*Examiner	Jus gale	voe	Date Considered	1	ムター	\mathcal{D}

Examiner: Initial il reference considered, whether or not citation is in conformance with MPEP 509; Draw tine through citation if not in conformance and not considered. Include copy of this form with next communication to application.

INFORM	MATION DISON DSURE	ATTY.	DOCKET NO.	SERIAL	NO.				
CITATION T		340-80		10/68	10/686,520				
	•	APPLIC	CANT						
PE		KOC	HERGIN et al.						
	govered sheets if necessary)	FILING		TC/A.U.					
,	=	160	ctober 2003	•0977	200	77			
2 8 2004	털	100	Ctober 2005	2872	<u> </u>				
INITIAL	7	·	J.S. PATENT DOCUMENTS	;					
CHARLES A							FILING		
PHITIAL	DOCUMENT NUMBER 4,874,484	10/1989	NAME Foell et al.		CLASS 438	SUBCLASS	IF APPRO	JPHI	
auc	5,262,021	11/1993	V. Lehmann et al		265	655			
1	5,348,627	09/1994	Propst et al.	·	205	655			
	5,431,766	07/1995	Propst et al.		156	345.15			
 	5,544,772	08/1996	Soave et al.		216	2			
 	5,645,684	07/1997	Keller		14%	33.2		_	
 	5,987,208	11/1999	Grunig		385	146			
 	5,997,713	12/1999	Beetz, Jr. et al.		205	124		_	
	6,521,149	02/2003	Mearini et al.		264	81			
uk	6,526,191	02/2003	Geusic et al.		385	14			
)	-					
			7						
		-							
			1						
		FOF	REIGN PATENT DOCUMEN	TS					
	DOCUMENT	DATE	COUNTRY		CLASS	SUBCLASS	TRANS	LATI N	
	3717851	UATE			CLASS	3080033	150		
			Germany						
me	4202454		Germany	·				-	
			- / 					\vdash	
			- /					-	
	- 		 					┝	
					·			-	
	<u> </u>		 					┢	
-			 						
			· · · · · · · · · · · · · · · · · · ·						
						لــــــا	<u> </u>	<u></u>	
	OTHER DO	CUMENT	S (including Author, Title, Da	te, Pertinent p	ages, et	e.)			
WE	Lehmann et al., Optical s	hortpass file	ers based on macroporous silic	on Appl. Phys. I	Lett. V 7	8, N.5, Jan. 2			
			al photonic crystals based on M	facroporous sili	con with	modulated p	ore diam	eter	
ul	Appl. Phys. Lett. V 78, N	1.9, Feb. 200	01						
_		lectrochemi	cal etching technique for n-type	silicon," Senso	rs and A	ctuators A 9	7-98 (20	02).	
<u>«</u>	720-724	- and Ord	and Massanan Campaign :	T CD! "	1 :6:3	El - de l	C	10.75	
uc	pp. G70-G76 (2002)	om and Orde	ered Macropore Formation in p-	T Abe Silicou'	s. of the	Electrochem	. 3 <i>0</i> C., 19	1) KI	
	85. 010-010 (500F)								

Examiner: Initial if reference considered, whether or not citation is in conformance with NPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Date Considered

*Examiner

INFORMATION DISCLOSURE	ATTY, DOCKET NO.	SERIAL NO.	
CITATION	340-80	10/686,520	
OIPER	APPLICANT		
ncr () 8 2004 w	KOCHERGIN et al.		
(Use several prote it necessary)	FILING DATE	TC/A.U.	
I SOCULAÇÃO	16 October 2003	2812 2 883	

U.S. PATENT DOCUMENTS

			J.S. PATENT DOCUMENTS			Ell INC	DATE
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS		
inc	4,689,021	08/1987	Burrus et al.	434	234		
Coul	5,262,021	11/1993	Lehmann et al.	205	655		
nuc	6,468,823	10/2002	Scherer et al.	438	3/		
al	6,483,640	11/2002	Torpecci et al.	358	54/		
			1				
			·/				
		-	/				
	<u> </u>					_	
			<u> </u>				
			1/				
		FO	REIGN PATENT DOCUMENTS				
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION NO
· · · · · · · · · · · · · · · · · · ·	DOCUMENT	DATE	CONINI	CEASS	1	163	, NO
	<u> </u>				 		
•	1		1 /				
			 /				
	OTHER DOC!	IMENTS (ochuding Author Title Date Partin	ant names a			
	OTHER DOCU	JMENTS (I	nicluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCL	JMENTS (I	nicluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCK	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCK	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCU	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCU	JMENTS (I	nicluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCU	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCL	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
	OTHER DOCU	JMENTS (I	ncluding Author, Title, Date, Pertin	ent pages, e			
Examiner		JMENTS (I	ncluding Author, Title, Date, Pertin				

Examiner: tritial if reference considered, whether or not citation is in conformance with MPEP 609; Oraw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

*Examiner | Comparison | Date Considered | -18-0 |

Examiner: Initial II reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation II not in conformance and not considered. Include copy of this form with next communication to application.

•	•		
Sheet	2 of 1		
INF	ORMATION DIS OSURE	ATTY, DOCKET NO.	SERIAL NO.
	CITATION	340-80	10/686,520
		APPLICANT	
	•	KOCHERGIN et al.	
	(Use several sheets if necessary)	FILING DATE	TC/A.U.
	,,,		-2872 C883
		16 October 2003	-2012 COB
	OTUED DOC	TIMERITE (including Autho	or, Title, Date, Pertinent pages, etc.)
	S Langa et al. "Observation	on of crossing pores in anodic	ally etched n-GaAs," Appl. Phys. Lett. 78(8), pp.1074-1076,
cruk	(2001).	on or erosom's pores in another	
			s: formation, properties, and comparison to silicon", Phys. Stat.
	Sol. A, 197 (1), pp. 61-70 (2003)	THE VIEW COLUMN TO THE COLUMN
como	M. Christophersen et al., " 197 (1), pp. 197-203, (200		on and pores in III-V compound materials", Phys. Stat. Sol. A,
our	H. Foll et al., 'Pores in III	-V Semiconductors", Adv. Me	uerials, Review, 2003, 15, pp.183 - 198, (2003)
and			"Single crystalline 2D porous arrays obtained by self
<u>ou</u>	organization in n-InP' (pp.		Daniel Ciliana Lauran II I Carre County 60 North Walland
ac	Amsterdam, p. 721-726 (1)		Porous Silicon Layers," J. Cryst. Growth, 68, North-Holland,
	D 77 E	tching: A Means to Enhance	the Photo response of Indirect Semiconductors," Adv. Mater., 7,
out	p. 739-742 (1995)		
MC	P.A. Kohl et al., J. Electron	chem. Soc., 130, p. 2288 (198	
me	Schmuki P. et al., Physica		ion on n-InP," 182 (1), pp. 51-61, (2000) ent Morphologies during Anodic Etching of n-InP,"
out out	J Electrochem. Soc. Lett.,		ent Morbinologies during Andrie Eurinig of 11-144,
	S. Langa et al., Phys. Stat.	Sot. (A), 195 (3), "Electroche	mical pose stehing in Oc," R4-R6 (2003)
	Macleod H.A., Thin-Film	Opiteal Filters, 3rd ed., Institu	ne of Physics Publishing, 2001
one	D.J. Lockwood et al., "Opt	ical properties of porous GaA	s," Physica E, 4, pp. 102-110 (1999)
Coul	Schmulki, P. et al., 'Forma	ition of porous layers on InSb	(100) by anodization," Phys. Stat. Sol. (a) 197, No. 1, pp. 71-76
and		scillations - an emergent pro	perty at high density pore growth," Phys. Stat. Sol. (a) 197, No. 1,
in	pp. 186-191 (2003)		
	- 		
		/	
	- 	-/	
	 	-/	

*Examiner	Ohtalund	Date Considered	1-18-05
Examiner	10h raws	Date Considered	

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.